



Attorney's Docket No. 42390P5783D

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of:

Steven N. Towle

Application No.: 10/082,997

Filed: February 25, 2002

For: METHOD FOR IMPROVING THERMAL
STABILITY OF FLUORINATED AMORPHOUS
CARBON LOW DIELECTRIC
CONSTANT MATERIALS

Commissioner for Patents

P.O. Box 1450

Alexandria, Virginia 22313-1450

Examiner: McDonald, Rodney Glenn

Art Unit: 1753

RECEIVED

DEC 15 2003

TC 1700

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 together with copies of the documents cited on that form. It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450 on December 3, 2003

(Date of Deposit)

Claire Walters

(Typed or printed name of person mailing correspondence)

Claire Walters 12/3/2003

(Signature of person mailing correspondence)

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

Pursuant to 37 C.F.R. § 1.97, this Information Disclosure Statement is being submitted under one of the following (as indicated by an "X" to the left of

12/10/2003 SSESHE1 00000102 10082997 180.00 0P 01 FC:1806

the appropriate paragraph):

_____ 37 C.F.R. §1.97(b).

X 37 C.F.R. §1.97(c). If so, then enclosed with this Information Disclosure Statement is one of the following:

_____ A statement pursuant to 37 C.F.R. §1.97(e) or

X A check for \$180.00 for the fee under 37 C.F.R. § 1.17(p).

_____ 37 C.F.R. §1.97(d). If so, then enclosed with this Information Disclosure Statement are the following:

- (1) A statement pursuant to 37 C.F.R. §1.97(e); and
- (2) A check for \$180.00 for the fee under 37 C.F.R. §1.17(p) for submission of the Information Disclosure Statement.

If there are any additional charges, please charge Deposit Account No. 02-2666.

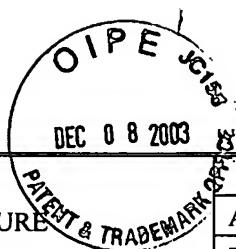
Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: 12/3, 2003


Heather M. Molleur
Reg. No. 50,432

12400 Wilshire Blvd.
Seventh Floor
Los Angeles, CA 90025
(408) 720-8300



Substitute for Form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known	
			Application Number	10/082,997
			Filing Date	February 25, 2002
			First Named Inventor:	Steven N. Towle
			Art Unit	1753
			Examiner Name	McDonald, Rodney Glenn
Sheet	1	of 1	Attorney Docket Number	42390P5783D

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		ANNEN, A., ET AL., Erosion of amorphous hydrogenated boron-carbon thin films, Journal of Nuclear Materials 231 (1996) pgs. 151-154, © 1996 Elsevier Science, B.V.	
		ENDO, KAZUHIKO, ET AL., Fluorinated amorphous carbon thin films grown by helicon plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, Appl. Phys. Lett. 68 (20) 13 May 1996, pgs. 2864-2866, © American Institute of Physics.	
		ENDO, KAZUHIKO, ET AL., Fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, J. Appl. Phys. 78 (2), 15 July 1995, pgs. 1370-1372, © 1995 American Institute of Physics.	
		ENDO, KAZUHIKO, ET AL., Nitrogen doped fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, Appl. Phys. Lett. 68 (25), 17 June 1996, pgs. 3656-3658 © 1996 American Institute of Physics.	
		MATSUBARA, Y., ET AL., Low-k Fluorinated Amorphous Carbon Interlayer Technology for Quarter Micron Devices, ULSI Device Development Labs, *Microelectronic Res. Labs., **VLSI Manufacturing Engineering Division, NEC Corporation, 1120 Shimokuzawa, Sagami-hara, Kanagawa, 229, Japan, 4 pages, No Date.	
		SHARAPOV, V.M., ET AL., Erosion of a-B/C : H films under deuterium plasma irradiation, Journal of Nuclear Materials 220-222 (1995) 930-933, pgs. 930-933, © 1995 Elsevier Science B.V.	
		YAMAKI, T., ET AL., Thermal desorption spectroscopy of boron/carbon films after keV deuterium irradiation, Journal of Nuclear Materials 217 (1994) 154-160, pgs. 154-160, © 1994 Elsevier Science B.V.	

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SENT FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.